

January 2015

FFB2222A / FMB2222A / MMPQ2222A NPN Multi-Chip General-Purpose Amplifier

Description

This device is for use as a medium power amplifier and switch requiring collector currents up to 500 mA. Sourced from process 19.

Block Diagram

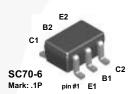


Figure 1. FFB2222A Device Package

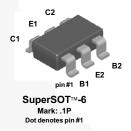


Figure 3. FMB2222A Device Package



Figure 5. MMPQ2222A Device Package

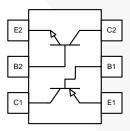


Figure 2. FFB2222A Internal Connection

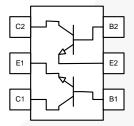


Figure 4. FMB2222A Internal Connection

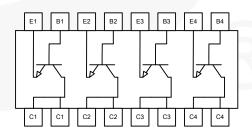


Figure 6. MMPQ2222A Internal Connection

Ordering Information

| Part Number | Top Mark | Package | Packing Method |
|-------------|---------------------|---------|----------------|
| FFB2222A | FFB2222A .1P | | Tape and Reel |
| FMB2222A | 22A .1P SSOT 6L | | Tape and Reel |
| MMPQ2222A | MMPQ2222A MMPQ2222A | | Tape and Reel |

Absolute Maximum Ratings(1)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^{\circ}\text{C}$ unless otherwise noted.

| Symbol | Parameter | Value | Unit |
|-----------------------------------|--|-------------|------|
| V _{CEO} | Collector-Emitter Voltage | 45 | V |
| V _{CBO} | Collector-Base Voltage | 75 | V |
| V _{EBO} | Emitter-Base Voltage | 5.0 | V |
| I _C | Collector Current - Continuous | 500 | mA |
| T _J , T _{STG} | Operating and Storage Junction Temperature Range | -55 to +150 | °C |

Note:

1. These ratings are based on a maximum junction temperature of 150°C. These are steady-state limits. Fairchild Semiconductor should be consulted on applications involving pulsed or low-duty cycle operations.

Thermal Characteristics(2)

Values are at $T_A = 25$ °C unless otherwise noted.

| Symbol | Parameter | Max. | | | Unit |
|------------------|--|----------|----------|-----------|-------|
| Syllibol | | FFB2222A | FMB2222A | MMPQ2222A | Oilit |
| Б | Total Device Dissipation | 300 | 700 | 1,000 | mW |
| P_{D} | Derate Above 25°C | 2.4 | 5.6 | 8.0 | mW/°C |
| R _{θJA} | Thermal Resistance, Junction-to-Ambient | 415 | 180 | | |
| | Thermal Resistance, Junction-to-Ambient, Effective 4 Dies | | | 125 | °C/W |
| | Thermal Resistance, Junction-to-Ambient, Each Die | | | 240 | |

Note:

2. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

Electrical Characteristics

Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

| Symbol | Parameter | Conditions | Min. | Тур. | Max. | Unit |
|-----------------------|---|---|------|------|------|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage ⁽³⁾ | I _C = 10 mA, I _B = 0 | 40 | | | V |
| V _{(BR)CBO} | Collector-Base Breakdown Voltage | $I_C = 10 \mu A, I_E = 0$ | 75 | | | V |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | $I_E = 10 \mu A, I_C = 0$ | 5.0 | | | V |
| I _{CBO} | Collector Cut-Off Current | $V_{CB} = 60 \text{ V}, I_{E} = 0$ | | | 10 | nA |
| I _{EBO} | Emitter Cut-Off Current | $V_{EB} = 3.0 \text{ V}, I_{C} = 0$ | | | 10 | nA |
| | | I _C = 0.1 mA, V _{CE} = 10 V | 35 | | | |
| | | $I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}$ | 50 | | | |
| h | DC Current Gain | I _C = 10 mA, V _{CE} = 10 V | 75 | | | |
| h _{FE} | | $I_C = 150 \text{ mA}, V_{CE} = 10 \text{ V}^{(3)}$ | 100 | | 300 | |
| | | $I_C = 150 \text{ mA}, V_{CE} = 1.0 \text{ V}^{(3)}$ | 50 | | | |
| | | $I_C = 500 \text{ mA}, V_{CE} = 10 \text{ V}^{(3)}$ | 40 | | | |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage ⁽³⁾ | I _C = 150 mA, I _B = 15 mA | | | 0.3 | V |
| | Collector-Entitler Saturation Voltage | $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$ | | | 1.0 | |
| \/ (aat) | Base-Emitter Saturation Voltage ⁽³⁾ | I _C = 150 mA, I _B = 15 mA | | | 1.2 | V |
| V _{BE} (sat) | base-Emilier Saturation Voltage | $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$ | | | 2.0 | v |
| f_{T} | Current Gain - Bandwidth Product | I _C = 20 mA, V _{CE} = 20 V, f = 100 MHz | \ | 300 | | MHz |
| C _{obo} | Output Capacitance | V _{CB} = 10 V, I _E = 0, f = 100 kHz | | 4.0 | | pF |
| C _{ibo} | Input Capacitance | V _{EB} = 0.5 V, I _C = 0, f = 100 kHz | | 20 | | pF |
| NF | Noise Figure | I_C = 100 μA, V_{CE} = 10 V, R_S = 1.0 kΩ, f = 1.0 kHz | | 2.0 | | dB |
| t _d | Delay Time | $V_{CC} = 30 \text{ V}, V_{BE(OFF)} = 0.5 \text{ V},$ | | 8 | | ns |
| t _r | Rise Time | I _C = 150 mA, I _{B1} = 15 mA | | 20 | | ns |
| t _s | Storage Time | $V_{CC} = 30 \text{ V}, I_{C} = 150 \text{ mA},$ | | 180 | | ns |
| t _f | Fall Time | I _{B1} = I _{B2} = 15 mA | | 40 | | ns |

Note:

3. Pulse test: pulse width \leq 300 μ s, duty cycle \leq 2.0%.

Typical Performance Characteristics

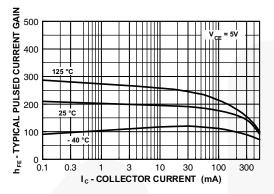


Figure 7. Typical Pulsed Current Gain vs. Collector Current

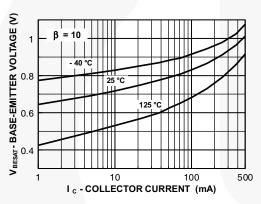


Figure 9. Base-Emitter Saturation Voltage vs. Collector Current

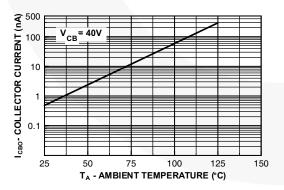


Figure 11. Collector Cut-Off Current vs.
Ambient Temperature

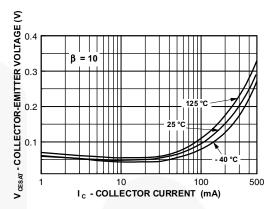


Figure 8. Collector-Emitter Saturation Voltage vs. Collector Current

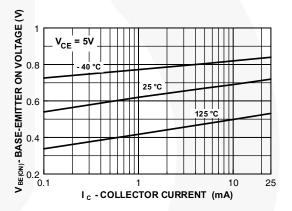


Figure 10. Base-Emitter On Voltage vs. Collector Current

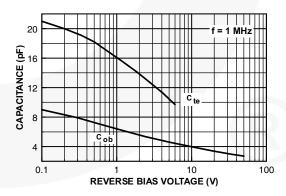


Figure 12. Emitter Transition and Output Capacitance vs. Reverse Bias Voltage

Typical Performance Characteristics (Continued)

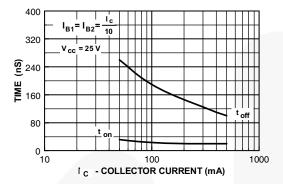


Figure 13. Turn-On and Turn-Off Times vs. Collector Current

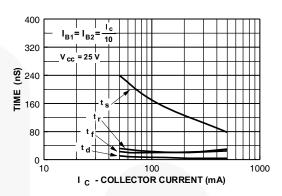


Figure 14. Switching Time vs. Collector Current

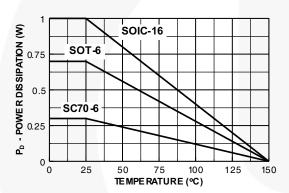


Figure 15. Power Dissipation vs. Ambient Temperature

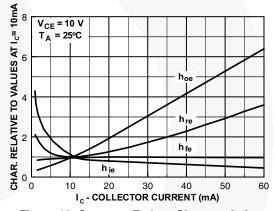


Figure 16. Common Emitter Characteristics

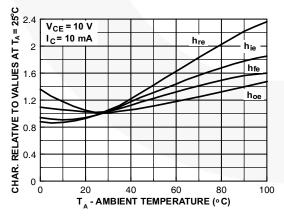


Figure 17. Common Emitter Characteristics

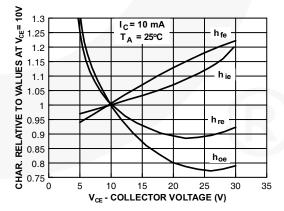


Figure 18. Common Emitter Characteristics

Test Circuits

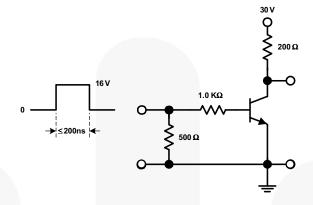


Figure 19. Saturated Turn-On Switching Time

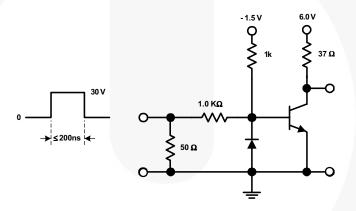


Figure 20. Saturated Turn-Off Switching Time

Physical Dimensions

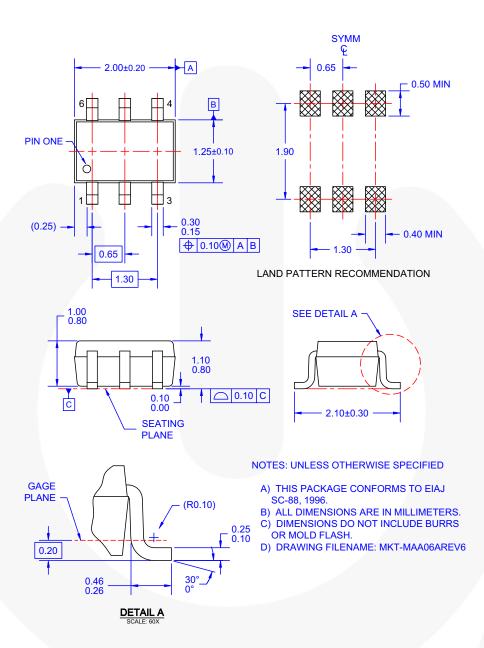


Figure 21. 6-LEAD, SC70, EIAJ SC-88, 1.25 MM WIDE

SYMM Ę 0.95 0.95 3.00 2.80 A 1.00 6 В 3.00 2.60 2.60 1.70 1.50 3 -0.50 0.300.95 0.70 MIN **⊕** 0.20**M** C A B 1.90 LAND PATTERN RECOMMENDATION (0.30) -SEE DETAIL A 1.10 MAX 0.20 0.08 Ċ 0.10 △ 0.10 C NOTES: UNLESS OTHERWISE SPECIFIED GAGE PLANE THIS PACKAGE CONFORMS TO JEDEC MO-193. VAR. AA, ISSUE C, DATED JANUARY 2000. ALL DIMENSIONS ARE IN MILLIMETERS. 0.25 SEATING PLANE -0.60 REF DETAIL A MA06AREVD

Figure 22. 6-LEAD, SUPERSOT-6, JEDEC MO-193, 1.6 MM WIDE

Physical Dimensions (Continued)

Physical Dimensions (Continued) 10.00 9.80 8.89 4.00 3.80 6.00 5.6 **PIN ONE** 0.51 **INDICATOR** 1.27 (0.30)**⊕** 0.25 **M** C B A LAND PATTERN RECOMMENDATION 1.75 MAX SEE DETAIL A 1.50 1.25 0.25 0.19 ○ 0.10 C -0.50 0.25 X 45° NOTES: UNLESS OTHERWISE SPECIFIED (R0.10) **GAGE PLANE** A) THIS PACKAGE CONFORMS TO JEDEC A) THIS PACKAGE CONFORMS TO JEDEC MS-012, VARIATION AC, ISSUE C. B) ALL DIMENSIONS ARE IN MILLIMETERS. C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS D) CONFORMS TO ASME Y14.5M-1994 E) LANDPATTERN STANDARD: SOIC127P600X175-16AM F) DRAWING FILE NAME: M16AREV12. (R0.10) 0.36 **SEATING PLANE** 0.90 0.50 (1.04)DETAIL A

Figure 23. 16-LEAD, SOIC, JEDEC MS-012, 0.150 inch, NARROW BODY





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